

HIGH CURRENT APPLICATION.

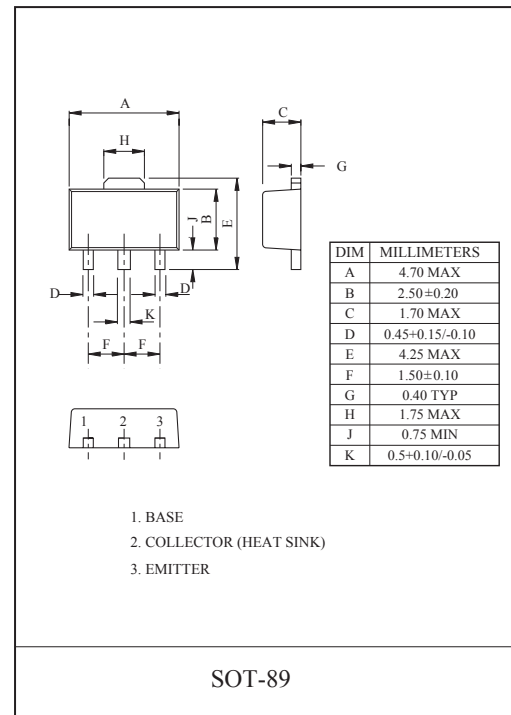
#### FEATURES

- 1W (Mounted on Ceramic Substrate).
- Small Flat Package.
- Complementary to KTA1663.

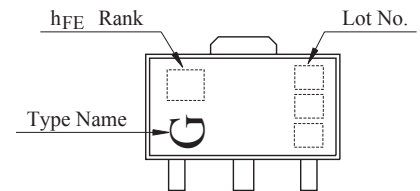
#### MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	30	V
Collector-Emitter Voltage	$V_{CEO}$	30	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	1.5	A
Base Current	$I_B$	0.3	A
Collector Power Dissipation	$P_C$	500	mW
	$P_C^*$	1	W
Junction Temperature	$T_j$	150	°C
Storage Temperature Range	$T_{stg}$	-55 ~ 150	°C

$P_C^*$  : KTC4375 mounted on ceramic substrate (250mm<sup>2</sup>x0.8t)



#### Marking



#### ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB}=30V, I_E=0$	-	-	100	nA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=5V, I_C=0$	-	-	100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	30	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	5	-	-	V
DC Current Gain	$h_{FE}$ (Note)	$V_{CE}=2V, I_C=500mA$	100	-	320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=1.5A, I_B=0.03A$	-	-	2.0	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE}=2V, I_C=500mA$	-	-	1.0	V
Transition Frequency	$f_T$	$V_{CE}=2V, I_C=500mA$	-	120	-	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=10V, I_E=0, f=1MHz$	-	-	40	pF

Note :  $h_{FE}$  Classification    O:100 ~ 200,    Y:160 ~ 320

